

## 30V N-Channel Power MOSFET



SOP-8

#### Pin Definition:

Source
 Source
 Source
 Drain
 Source
 Drain
 Gate

## **Key Parameter Performance**

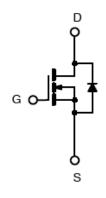
Parameter		Value	Unit	
$V_{DS}$		30	V	
R <sub>DS(on)</sub> (max)	V <sub>GS</sub> = 10V	18	mΩ	
	V <sub>GS</sub> = 4.5V	28		
$Q_g$		4.1	nC	

### **Ordering Information**

Part No.	Package	Packing		
TSM180N03CS RLG	SOP-8	2.5kpcs / 13" Reel		

**Note:** "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

## **Block Diagram**



N-Channel MOSFET

#### Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		$V_{DS}$	30	V
Gate-Source Voltage		$V_{GS}$	±20	V
Continuous Drain Current	Tc=25°C	- I <sub>D</sub>	9	Α
	Tc=100°C		5.7	А
Pulsed Drain Current (Note 1)		I <sub>DM</sub>	36	Α
Single Pulse Avalanche Energy (Note 2)		E <sub>AS</sub>	32	mJ
Power Dissipation @ T <sub>C</sub> = 25°C		$P_D$	2.5	W
Operating Junction Temperature		TJ	150	∘C
Storage Temperature Range		T <sub>STG</sub>	-55 to +150	°C

#### **Thermal Performance**

Parameter	Symbol	Limit	it Unit	
Thermal Resistance - Junction to Ambient	$R_{\Theta JA}$	50	°C/W	



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**Electrical Specifications** (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	30			V
5	$V_{GS} = 10V, I_D = 8A$	R <sub>DS(ON)</sub>		16	18	mΩ
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 5A$			23	28	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V <sub>GS(TH)</sub>	1.2	1.6	2	V
Zero Gate Voltage Drain Current	$V_{DS} = 30V, V_{GS} = 0V$				1	μΑ
	V <sub>DS</sub> = 24V, T <sub>J</sub> = 125°C	I <sub>DSS</sub>			10	
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Forward Transconductance (Note 3)	$V_{DS} = 10V, I_{D} = 5A$	g <sub>fs</sub>		4		S
Dynamic						
Total Gate Charge (Note 3,4)		$Q_g$		4.1		nC
Gate-Source Charge (Note 3,4)	$V_{DS} = 15V, I_{D} = 8A,$	$Q_{gs}$		1		
Gate-Drain Charge (Note 3,4)	$V_{GS} = 4.5V$	$Q_{gd}$		2.1		
Input Capacitance		C <sub>iss</sub>		345		pF
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	C <sub>oss</sub>		55		
Reverse Transfer Capacitance	7 I = 1.0IVIM2	C <sub>rss</sub>		32		
Switching						
Turn-On Delay Time (Note 3,4)		t <sub>d(on)</sub>		2.8		ns
Turn-On Rise Time (Note 3,4)	$V_{DD} = 15V, I_{D} = 1A,$	t <sub>r</sub>		7.2		
Turn-Off Delay Time (Note 3,4)	$V_{GS} = 10V, R_G = 6\Omega$	t <sub>d(off)</sub>		15.8		
Turn-Off Fall Time (Note 3,4)	]	t <sub>f</sub>		4.6		
Source-Drain Diode Ratings and Ch	aracteristic					
Maximum Continuous Drain-Source		ı			9	А
Diode Forward Current	Integral reverse diode in the MOSFET	I <sub>S</sub>			9	
Maximum Pulse Drain-Source Diode		I <sub>SM</sub>			36	Α
Forward Current						
Diode-Source Forward Voltage	$V_{GS} = 0V$ , $I_S = 1A$	$V_{SD}$			1	V

#### Note:

- 1. Pulse width limited by safe operating area
- 2. L=1mH,  $I_{AS}$ =8A,  $V_{DD}$ =25V,  $R_{G}$ =25 $\Omega$ , Starting  $T_{J}$ =25 $^{\circ}$ C
- 3. Pulse test: pulse width ≤300µs, duty cycle ≤2%
- 4. Switching time is essentially independent of operating temperature.

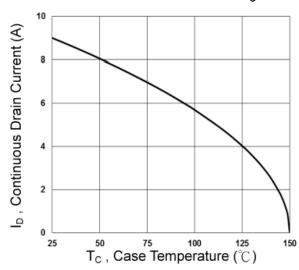


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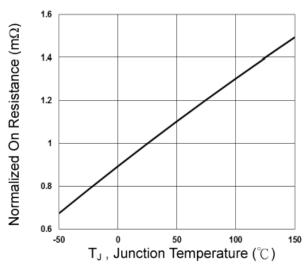


#### **Electrical Characteristics Curve**

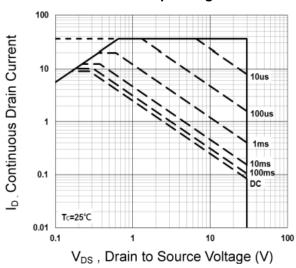
#### Continuous Drain Current vs. T<sub>C</sub>



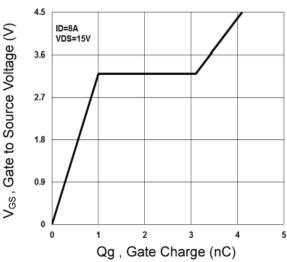
#### On-Resistance vs. Junction Temperature



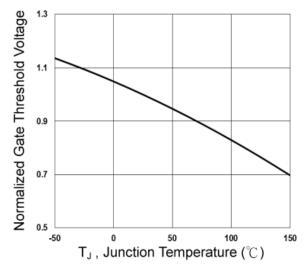
#### **Maximum Safe Operating Area**



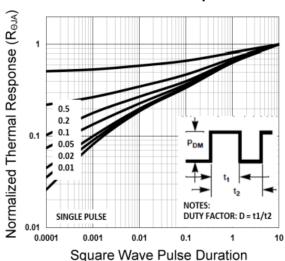
Gate Charge



#### Threshold Voltage vs. Junction Temperature



#### **Normalized Thermal Transient Impedance Curve**

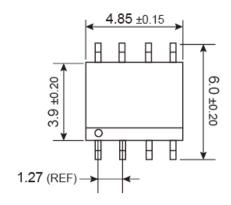


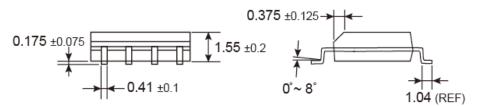


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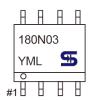
# **SOP-8 Mechanical Drawing**





Unit: Millimeters

## **Marking Diagram**



Y = Year Code

M = Month Code for Halogen Free Product (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

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L = Lot Code

Version: A14



# Pb RoHS

# TSM180N03CS 30V N-Channel Power MOSFET

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